



PATENT
9862-000016/US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: Yun-Jung LEE et al. CONF. NO.: 9195
SERIAL NO.: 10/632,825 GROUP: 2826
FILED: August 4, 2003 EXAMINER: Evan T. Pert
FOR: METHOD OF FORMING OXIDE LAYER USING ATOMIC
LAYER DEPOSITION METHOD AND METHOD OF FORMING
CAPACITOR OF SEMICONDUCTOR DEVICE USING THE
SAME

AMENDMENT AFTER FINAL

Customer Service Window
Randolph Building
401 Dulany Street
Alexandria, VA 22314
Mail Stop AF

December 7, 2005

*Please
enter.
EP 12/27/05*

Dear Sir:

Responsive to the Final Official Action dated October 17, 2005, the following amendments and remarks are respectfully submitted in connection with the above-referenced application.

Amendments to the claims begin on page 2 of this paper.

Remarks begin on page 13 of this paper.